AMENDMENTS TO THE CLAIMS:

1. (Amended) A semiconductor apparatus, comprising:

a substrate having a transistor formed thereon;

a ~~first electrode formed on~~ plurality of first capacitor electrodes secured to said substrate and ~~connected to said transistor~~;

a ~~second electrode formed on~~ plurality of second electrodes secured to said substrate and electrically separated from said first electrodes; and

an insulating film formed ~~on said substrate~~ so as to cover said first ~~electrode~~ electrodes and which is between the first electrodes and second electrodes,

wherein the first and second electrodes have a common bottom level and the plurality of second electrodes each have a top surface which is above a top surface of the first electrodes.

~~wherein, when a plane of said insulating film which is not on a side of said substrate is taken as a first plane, a surface facing said first plane of said first electrode is taken as a first surface, and a surface facing said first plane of said second electrode is taken as a second surface, a distance between a surface of said substrate and said second surface is larger than a distance between the surface of said substrate and said first surface.~~

2. (Amended) The semiconductor apparatus according to claim 1, wherein said ~~second surface~~ top surface of the second electrodes is substantially equivalent to a top surface of said insulating film.

3. (Amended) The semiconductor apparatus according to claim 1, wherein ~~the~~ a distance between ~~the~~ a top surface of said substrate and said ~~second surface~~ top surface of the second electrodes is larger than a distance between the top surface of said substrate and the top surface of said insulating film.

4. (Amended) The semiconductor apparatus according to claim 1, wherein said second electrodes are ~~is~~ fixed ~~in~~ to a constant potential.

5. (Amended) The semiconductor apparatus according to claim 1, wherein a plurality of said first electrodes are arranged in a matrix form, and said second ~~electrode is~~ electrodes are disposed between said plurality of first electrodes.

6. (Amended) The semiconductor apparatus according to claim 5, wherein ~~a~~ said plurality of ~~said~~ second electrodes are arranged in a matrix form.

7. (Amended) The semiconductor apparatus according to claim 1, wherein at least one of said first ~~electrode is~~ electrodes are connected to a first terminal of said transistor, and a

second terminal of said transistor is connected to a bit line and a capacitance element to which a potential is applied.

8. (Amended) The semiconductor apparatus according to claim 2, wherein said second ~~electrode is~~ electrodes are fixed ~~in~~ to a constant potential.

9. (Amended) The semiconductor apparatus according to claim 3, wherein said second ~~electrode is~~ electrodes are fixed ~~in~~ to a constant potential.

10. (Amended) The semiconductor apparatus according to claim 1, wherein said second ~~electrode is~~ electrodes are electrically connected to a corresponding pad electrode which is connected to a lead for taking a signal out.

11. (Amended) A semiconductor apparatus for recognizing a fingerprint, comprising:

~~a semiconductor substrate having a transistor;~~

a ~~first electrode formed on said~~ plurality of first capacitor electrodes secured to a semiconductor substrate ~~and connected to said transistor~~;

a ~~second electrode formed on~~ plurality of second electrodes secured to said semiconductor substrate and electrically separated from said first ~~electrode~~ electrodes; and

an insulating film formed on said semiconductor substrate so as to cover said ~~first electrode~~ plurality of first electrodes,

wherein the first and second electrodes have a common bottom level and the plurality of second electrodes each have a top surface which is above a top surface of the first electrodes.

~~wherein, when a plane of said insulating film on which said fingerprint is placed is taken as a first plane, a surface facing said first plane of said first electrode is taken as a first surface, and a surface facing said first plane of said second electrode is taken as a second surface, a distance between a surface of said semiconductor substrate and said second surface is larger than a distance between the surface of said semiconductor substrate and said first surface.~~

12. (Amended) The semiconductor apparatus according to claim 11, wherein said ~~second surface~~ top surface of said second electrodes is substantially equivalent to a top surface of said insulating film.

13. (Amended) The semiconductor apparatus according to claim 11, wherein ~~the~~ a distance between ~~the~~ a top surface of said semiconductor substrate and said ~~second surface~~ top surface of said second electrodes is larger than a distance between the top surface of said semiconductor substrate and the top surface of said insulating film.

14. (Amended) The semiconductor apparatus according to claim 11, wherein said second electrodes are ~~electrode is~~ fixed ~~in~~ to a constant potential.

15. (Amended) The semiconductor apparatus according to claim 11, wherein a plurality of said first electrodes are arranged in a matrix form, and said second ~~electrode is~~ electrodes are disposed between said plurality of first electrodes.

16. (Amended) The semiconductor apparatus according to claim 15, wherein ~~a~~ said plurality of ~~said~~ second electrodes are arranged in a matrix form.

17. (Amended) The semiconductor apparatus according to claim 11, wherein at least one of said first electrodes are ~~electrode is~~ connected to a first terminal of ~~said~~ a transistor formed on said substrate, and a second terminal of said transistor is connected to a bit line and a capacitance element to which a potential is applied.

18. (Amended) The semiconductor apparatus according to claim 12, wherein said second electrodes ~~is~~ are fixed ~~in~~ to a constant potential.

19. (Amended) The semiconductor apparatus according to claim 13, wherein said second electrodes ~~is~~ are fixed ~~in~~ to a constant potential.

20. (Amended) The semiconductor apparatus according to claim 11, wherein said second electrodes ~~is~~ are respectively electrically connected to a corresponding pad electrode which is connected to a lead for taking a signal out.